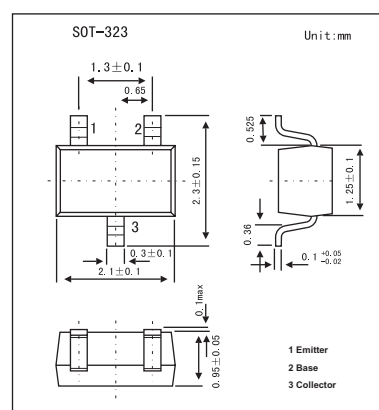


Silicon PNP Epitaxial Planar Type

2SA1532

■ Features

- High transition frequency fr.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-30	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-30	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Base-emitter saturation voltage	V _{BE}	V _{CE} = -10 V, I _C = -1 mA		-0.7		V
Collector-base cutoff current	I _{CB0}	V _{CB} = -10 V, I _E = 0			-0.1	μA
Collector-emitter cutoff current	I _{CEO}	V _{CE} = -20 V, I _B = 0			-100	μA
Emitter-base cutoff current	I _{EBO}	V _{EB} = -5 V, I _C = 0			-10	μA
Forward current transfer ratio	h _{FE}	V _{CB} = -10 V, I _E = 1 mA	50		220	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -1 mA		-0.1		V
Transition frequency	f _T	V _{CB} = -10 V, I _E = 1 mA, f = 200 MHz	150	300		MHz
Noise voltage	N _F	V _{CB} = -10 V, I _E = 1 mA, f = 5 MHz		2.8	4.0	dB
Reverse transfer impedance	Z _{rb}	V _{CB} = -10 V, I _E = 1 mA, f = 2 MHz		22	60	Ω
Common-emitter reverse transfer capacitance	C _{re}	V _{CB} = -10 V, I _E = 1 mA, f = 10.7 MHz		1.2	2.0	pF

■ hFE Classification

Marking	E		
	A	B	C
hFE	50~100	70~140	110~220